INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
YO999-408 CIP	Not Yet Assigned

Applicant(s)
Cohen et al.

Filing Date	Group Art Unit
Concurrently Herewith	Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK		6,054,386	04/2000	Prabhakar	—	—	
EX		6,169,005	01/2001	Kepler	—	—	
EK		5,994,191	11/1999	Xiang	—	—	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	NO

OTHER DOCUMENTS   *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER	DATE CONSIDERED
Erik Kistler	2/1/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and r considered. Include copy of this form with next communication to applicant.

SHEET   1   OF   1

INFORMATION DISCLOSURE CITATION		Docket Number (Optional) YO999-4 IP	Application Number 09/902,483				
(Use several sheets if necessary)		Applicant(s) Cabral, Jr., et al.					
		Filing Date July 11, 2001	Group Art Unit 2813				

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK		5,773,331	6/30/98	Solomon et al.	—	—	
EK		4,912,542	3/27/90	Suguro	—	—	
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FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	NO

OTHER DOCUMENTS _(Including Author, Title, Date, Pertinent Pages, Etc.)_

EK	U.S. Patent Application No. 09/515,033, YOR900-0044US1, "Method For Self-Aligned Formation Of Silicide Contacts Using Metal Silicon Alloys For Limited Silicon Consumption And For Reduction Of Bridging", pp. 1-21, and Figs. 1A-3B. now U.S. Patent 6,323,130	
EK	Lisa T. Su, Melanie J. Sherony, Hang Hu, James E. Chung, and Dimitri A. Antoniadis; "Optimization of Series Resistance in Sub-0.2, um SOI MOSFET's; IEEE Electron Device Letters, Vol. 15, No. 9, September 1994; pages 363-365.	

EXAMINER	DATE CONSIDERED 2/1/02

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	INFORMATION DISCLOSURE CITATION *(Use several sheets if necessary)*	**Docket Number (Optional)** YO999-4 IP	**Application Number** 09/902,483

Docket Number (Optional) YO999-4 IP	**Application Number** 09/902,483
Applicant(s) Cabral, Jr. et al.	
Filing Date July 11, 2001	**Group Art Unit** 2813

*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
$\mathcal{E}\mathcal{L}$		T. Yoshitomi, M. Saito, T. Ohguro, M. Ono, H.S. Momose, and H. Iwai; "Silicided Silicon-Sidewall Source and Drain (S4D) structure for high-performance 75-nm gate length pMOSFETs; 1995 Symposium on VLSI Technology Digest of Technical Papers; 0-7803-2602-4/95; pages 11 and 12.
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EXAMINER		**DATE CONSIDERED**
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